


[Home](#) > [2N6673 \(#23623\)](#)

## 2N6673 (#23623)

### Products

- ▶ [Product Directory](#)
- ▶ [Applications Directory](#)
- ▶ [Parametric Search](#)

#### Overview

#### Diagrams

Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$			1.50	V
DC Current Gain	HFE	10.00		40.00	

Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	$V_{BR(CBO)}$			650.00	V
Collector Current (dc)	$I_C$			8.00	A
Collector-Emitter Voltage (Base Open)	$V_{CEO}$			400.00	V
Emitter-Base Voltage (Collector Open)	$V_{EBO}$			7.00	V
Power Dissipation, Total	$P_T$			150.00	W

This part can be found in the following product categories:

- ▶ [Discretes](#) ▶ [Transistors](#) ▶ [BJT \(BiPolar Junction Transistor\)](#) ▶ [PNP Transistor](#)
- ▶ [Non-Radiation Hardened Devices](#) ▶ [Transistors](#) ▶ [BJT \(BiPolar Junction Transistor\)](#) ▶ [NPN Transistor](#)

### Related Links

- [Technical support](#)
- [Sales Contacts](#)
- [Available Stock](#)
- [Sales Contacts](#)
- [RFQ/Samples](#)